Ashutosh Mahajan

List of Publications by Year
in descending order

17 papers	140 citations	1684188 5 h-index	1281871 11 g-index
20 all docs	20 docs citations	20 times ranked	110 citing authors

#	Article	IF	Citations
1	An epidemic model SIPHERD and its application for prediction of the spread of COVID-19 infection in India. Chaos, Solitons and Fractals, 2020, 140, 110156.	5.1	58
2	Estimation of undetected symptomatic and asymptomatic cases of COVID‐19 infection and prediction of its spread in the USA. Journal of Medical Virology, 2021, 93, 3202-3210.	5.0	31
3	Gravitational collapse from smooth initial data with vanishing radial pressure. Classical and Quantum Gravity, 2005, 22, 271-282.	4.0	10
4	Finite Element Modeling of Fowler–Nordheim Program-Erase Process in High- k Interpoly Dielectric Flash Memories. IEEE Transactions on Electron Devices, 2016, 63, 4729-4736.	3.0	8
5	Cosmic censorship in higher dimensions. II.. Physical Review D, 2005, 72, .	4.7	6
6	Critical Collapse of Einstein Cluster. Progress of Theoretical Physics, 2007, 118, 865-878.	2.0	4
7	Finite-Element Modeling of Retention in Nanocrystal Flash Memories With High- k Interpoly Dielectric Stack. IEEE Transactions on Electron Devices, 2017, 64, 4897-4903.	3.0	4
8	Review on long afterglow nanophosphors, their mechanism and its application in round-the-clock working photocatalysis. Methods and Applications in Fluorescence, 2022, 10, 032001.	2.3	4
9	An analytical model for electron tunneling in triangular quantum wells. Semiconductor Science and Technology, 2021, 36, 055012.	2.0	3
10	Rebounce and black hole formation in a gravitational collapse model with vanishing radial pressure. General Relativity and Gravitation, 2007, 39, 825-838.	2.0	2
11	Analytical solutions for black-hole critical behaviour. General Relativity and Gravitation, 2007, 39, 1847-1854.	2.0	2
12	Efficient Modeling of Barrier Resistance for an Improved Lumped Element Model of GaN-Based MIS-HEMT Gate Stack. IEEE Journal of the Electron Devices Society, 2020, 8, 1145-1153.	2.1	1
13	Modeling of program/erase transient in heterogeneous SiNx charge trap flash memories. Superlattices and Microstructures, 2020, 144, 106577.	3.1	1
14	Correction in Active Cases Data of COVID-19 for the US States by Analytical Study. Disaster Medicine and Public Health Preparedness, 2022, 16, 2335-2338.	1.3	1
15	Finite element modeling of retention process in high-k interpoly dielectric nanocrystal flash memories. , 2016, , .		0
16	Modeling and Finite Element Simulation of Gate Leakage in Cylindrical GAA Nanowire FETs. , 2018, , .		0
17	Modeling of gate leakage in cylindrical gate-all-around transistors. Journal of Computational Electronics, 2021, 20, 1694-1701.	2.5	0